

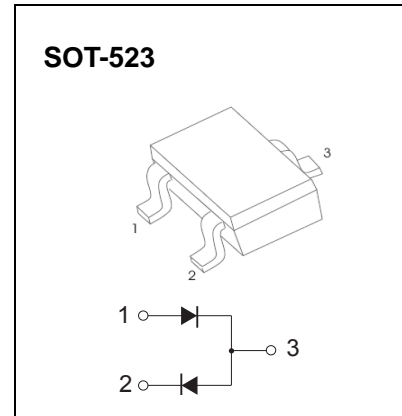
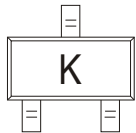
Plastic-Encapsulate Transistors

DA221T SWITCHING DIODE

FEATURES:

- Bias circuits
- Protection circuits

MARKING: K



Maximum Ratings @Ta=25°C

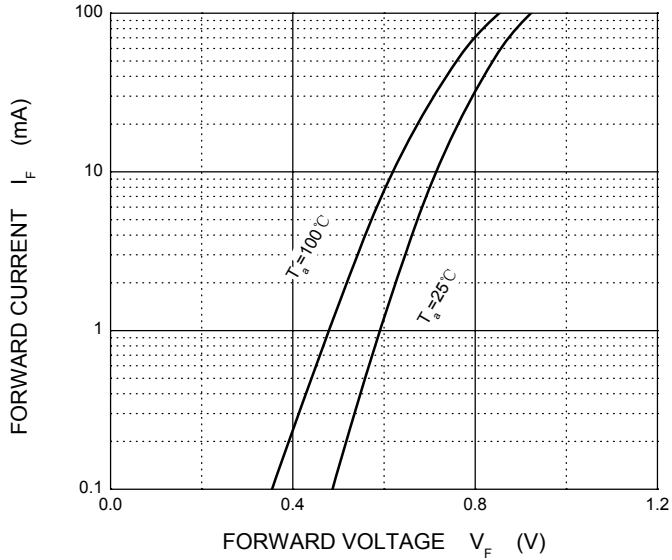
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	20	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	20	V
DC Blocking Voltage	V_R		V
Forward Continuous Current	I_{FM}	200	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Average Rectified Output Current	I_O	100	mA
Power Dissipation	P_D	150	mW
Thermal resistance From Junction to ambient	$R_{\theta JA}$	833	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	°C

Electrical Characteristics @Ta=25°C

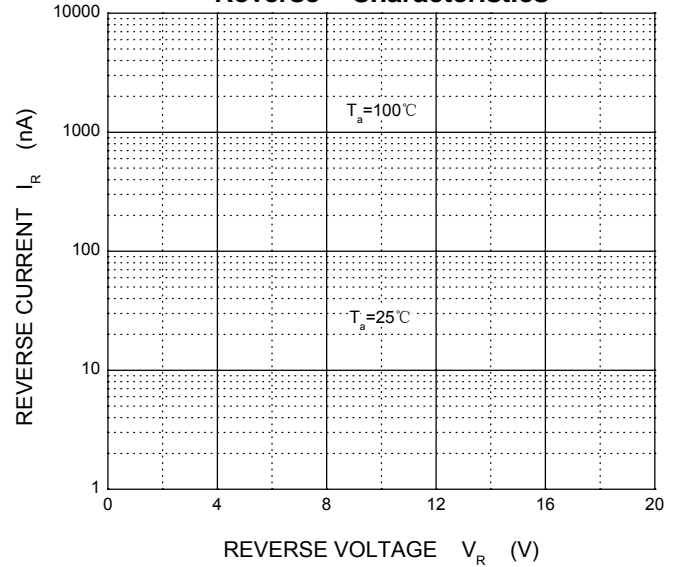
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	$V_{(BR)}$	20			V	$I_R=100\mu A$
Forward voltage	V_F			1	V	$I_F=10mA$
Reverse current	I_R			0.1	μA	$V_R=15V$

Typical Characteristics

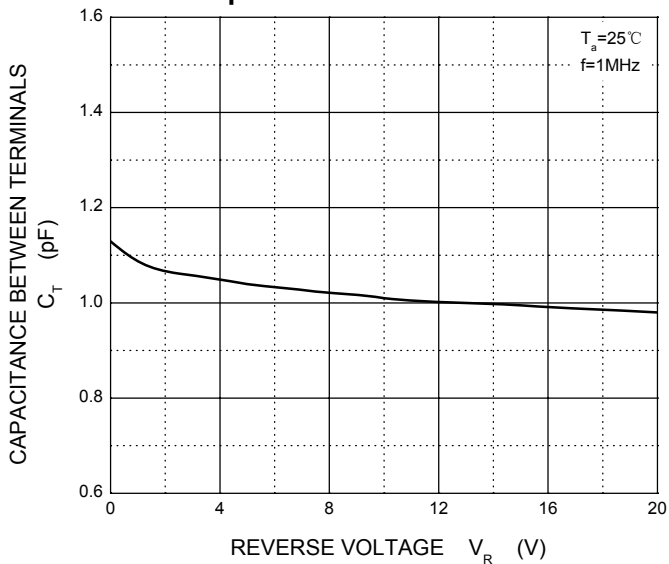
Forward Characteristics



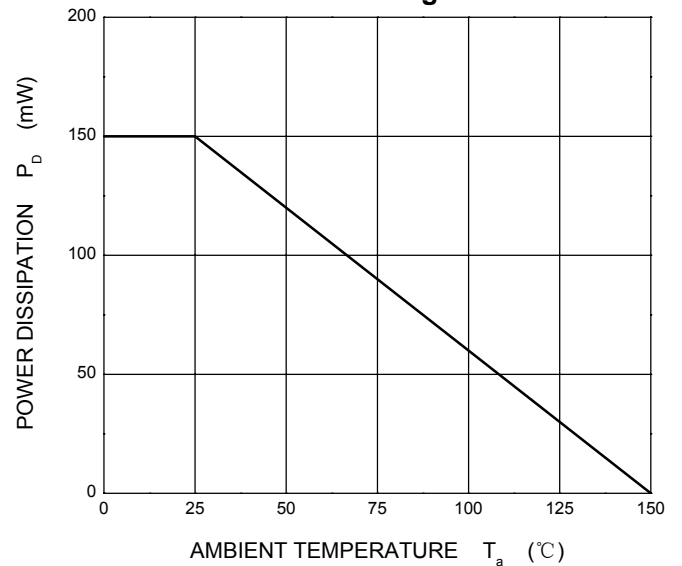
Reverse Characteristics



Capacitance Characteristics



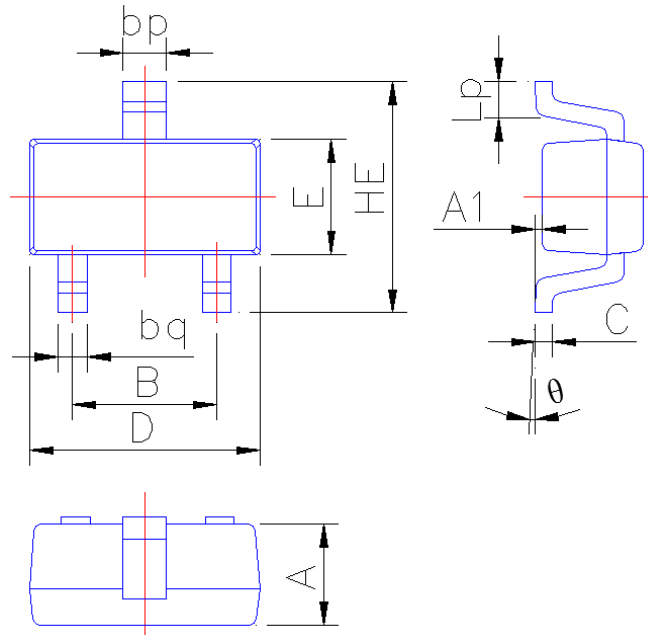
Power Derating Curve



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.80
A1	0.010	0.100
B	0.95	1.05
bp	0.26	0.40
bq	0.16	0.30
C	0.09	0.15
D	1.50	1.70
E	0.70	0.85
HE	1.45	1.75
Lp	0.16	0.36
θ	0°	5°